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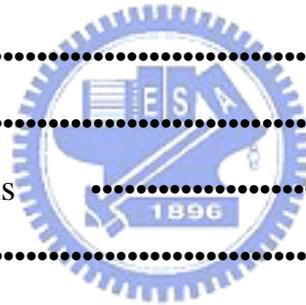
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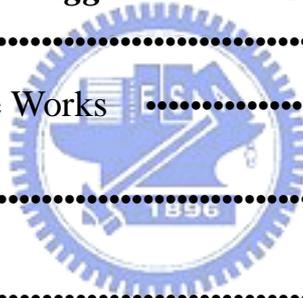


Table Captions

Table 1-1 Material requirements of high-k dielectrics

Table 1-2 illustrates dielectric constant and high-k materials barrier height of electron and holes.



Figure Captions

Chapter 1

Fig. 1-1 LSTP Logic Scaling-up of Gate Leakage Current Density Limit and of Simulated Gate Leakage due to Direct Tunneling.

Fig. 1-2 Illustrates dielectric constant and high-k materials barrier height of electron and holes.

Chapter 2

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